

In the Claims

1. (Currently Amended) A semiconductor package comprising:
 - an electrically insulating substrate layer;
 - a non-conductive layer disposed on the electrically insulating substrate layer; and,
 - a ~~metal or metal matrix composite~~ reflector layer disposed on the non-conductive layer,wherein the electrically insulating substrate layer includes at least one first metallized portion on a first surface thereof and at least one second metallized portion on a second surface thereof, said second surface opposite said first surface, and
 - wherein the reflector layer is made of a metal with a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of a material of the electrically insulating substrate layer.
2. (Original) The semiconductor package of claim 1, wherein the reflector layer includes a conical portion.
3. - 5. (Canceled).
6. (Original) The semiconductor package of claim 1, wherein the non-conductive layer is made of glass.
7. (Original) The semiconductor package of claim 6, wherein the glass has a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.
8. (Currently Amended) The semiconductor package of claim 7, wherein the glass and the material of the electrically insulating substrate layer both have a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the ~~material~~ metal of the reflector layer.

9. – 13. (Canceled).

14. (Currently Amended) A light emitting device comprising:

an electrically insulating substrate layer with at least one light emitting diode disposed thereon;

a non-conductive layer disposed on the electrically insulating substrate layer; and,

a ~~metal or metal matrix composite~~ reflector layer disposed on the non-conductive layer,

wherein the electrically insulating substrate layer includes at least one first metallized portion on a first surface thereof and at least one second metallized portion on a second surface thereof, said second surface opposite said first surface, and

wherein the reflector layer is made of a metal with a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of a material of the electrically insulating substrate layer.

15. (Previously Presented) The light emitting device of claim 14, wherein one of the at least one first and second metallized portions are coupled to the light emitting diode.

16. – 17. (Canceled).

18. (New) The semiconductor package of claim 1, wherein the reflector layer is made of a material comprising metal, said reflector layer material having a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.

19. (New) The semiconductor package of claim 1, wherein the reflector layer is made of a metal-composite material comprising metal and at least one other material, said metal-composite material having a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.

20. (New) The semiconductor package of claim 1, wherein the reflector layer is made of a metal-alloy, said metal-alloy having a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.

21. (New) The light emitting device of claim 14, wherein the reflector layer is made of a material comprising metal, said reflector layer material having a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.

22. (New) The light emitting device of claim 14, wherein the reflector layer is made of a metal-composite material comprising metal and at least one other material, said metal-composite material having a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.

23. (New) The light emitting device of claim 14, wherein the reflector layer is made of a metal-alloy, said metal-alloy having a coefficient of thermal expansion which is matched to a coefficient of thermal expansion of the material of the electrically insulating substrate layer.